

Graphene-Silicon Schottky Diodes

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Equation 1 of this paper should be

$$I = I_o (e^{V_{\text{bias}}/n_{\text{id}}k_{\text{B}}T} - 1)$$

not

$$I = I_o \left(\frac{eV_{\text{bias}}}{e^{n_{\text{id}}k_{\text{B}}T} - 1} \right)$$

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